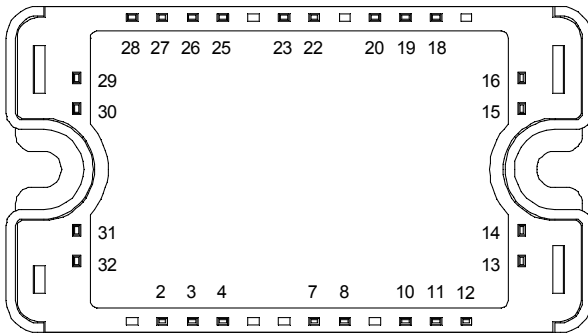
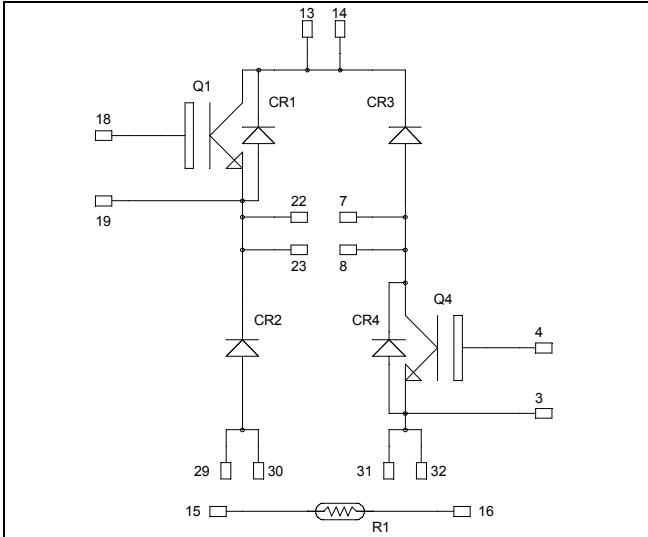


**Asymmetrical - Bridge
Trench + Field Stop IGBT4
Power module**

**$V_{CES} = 1200V$
 $I_C = 60A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	80
		$T_c = 80^\circ C$	60
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	100
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	280
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	100A @ 1100V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 1200\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 50\text{A}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.85 2.25	2.25	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.6\text{mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		2770		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		205		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		160		
Q_G	Gate charge	$V_{GE} = \pm 15\text{V}; V_{CE} = 600\text{V}$ $I_C = 50\text{A}$		0.38		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $I_C = 50\text{A}$ $R_G = 8.2\Omega$		130		ns
T_r	Rise Time			20		
$T_{d(off)}$	Turn-off Delay Time			300		
T_f	Fall Time			45		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $I_C = 50\text{A}$ $R_G = 8.2\Omega$		150		ns
T_r	Rise Time			35		
$T_{d(off)}$	Turn-off Delay Time			350		
T_f	Fall Time			80		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $I_C = 50\text{A}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	3.8 5.5		mJ
E_{off}	Turn-off Switching Energy	$R_G = 8.2\Omega$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	2.5 4.5		mJ
I_{sc}	Short Circuit data	$V_{GE} \leq 15\text{V}; V_{Bus} = 900\text{V}$ $t_p \leq 10\mu\text{s}; T_j = 150^\circ\text{C}$		200		A

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$			250	μA
I_F	DC Forward Current			90		A
V_F	Diode Forward Voltage	$I_F = 50\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.5 1.43	2.0	V
t_{rr}	Reverse Recovery Time	$I_F = 50\text{A}$ $V_R = 600\text{V}$ $di/dt = 1300\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	155 300		ns
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	4.8 10		μC
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.7 3.6		mJ

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	IGBT		0.53	°C/W	
		Diode		0.62		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		175	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

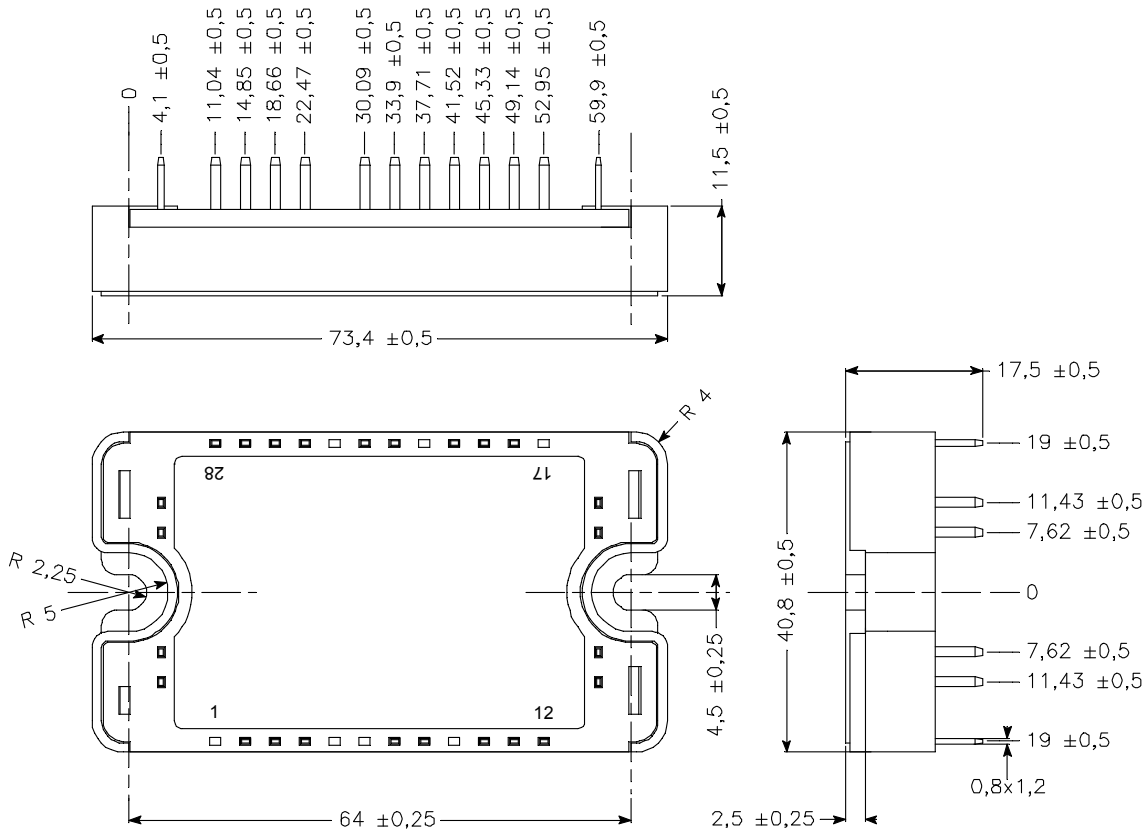
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

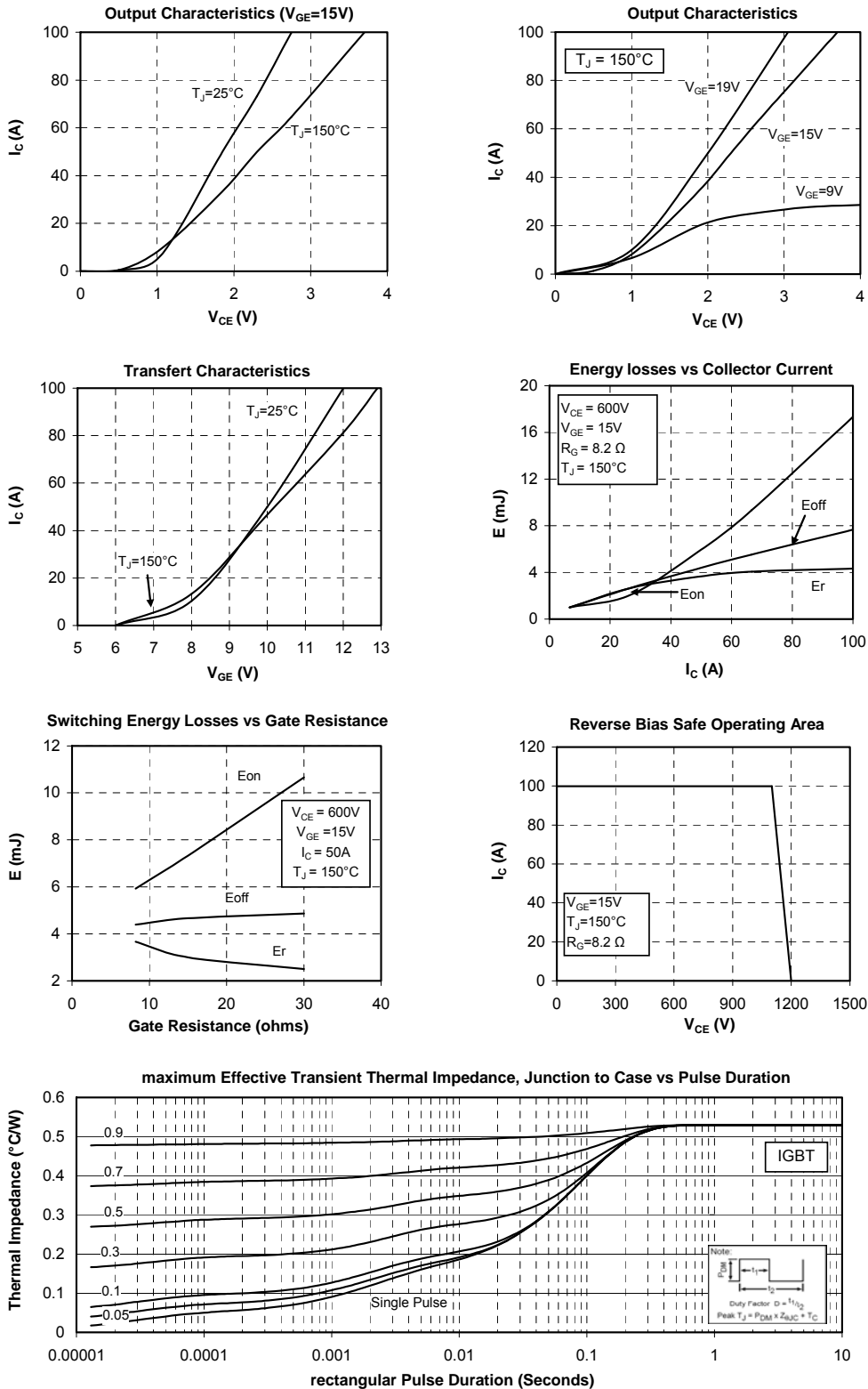
T: Thermistor temperature
 R_T: Thermistor value at T

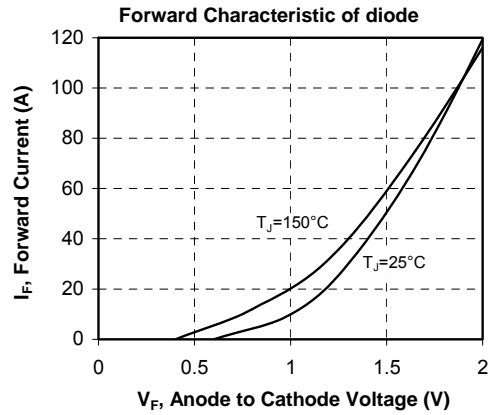
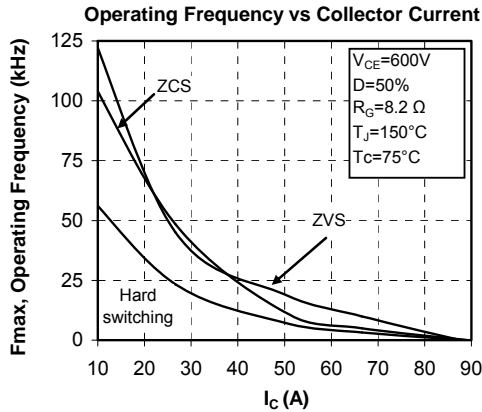
SP3 Package outline (dimensions in mm)



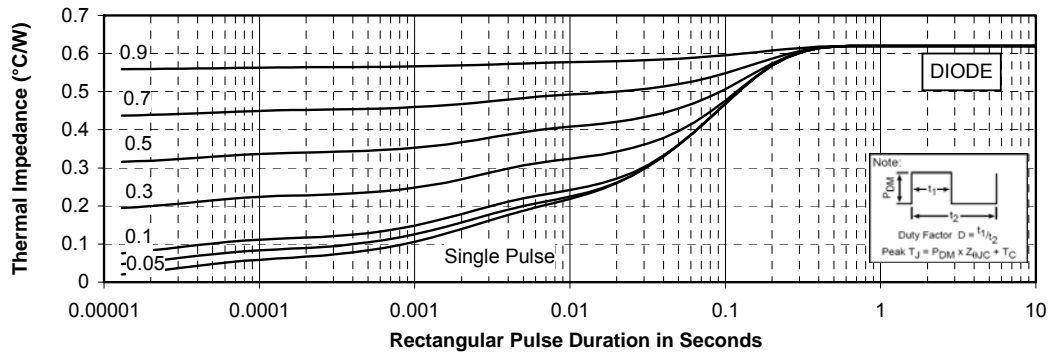
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve





maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.